VS-HFA90FA120

Vishay Semiconductors



HEXFRED[®] Ultrafast Soft Recovery Diode, 90 A



PRIMARY CHARACTERISTICS						
V _R	1200 V					
V _F (typical)	2.46 V					
t _{rr} (typical)	35 ns					
$I_{F(AV)}$ per module at T_{C}	90 A at 63 °C					
Package	SOT-227					

FEATURES

- · Fast recovery time characteristic
- Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- · Designed and qualified for industrial level
- UL approved file E78996
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

The dual diode series configuration (VS-HFA90FA120) is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 Gen 2 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Cathode to anode breakdown voltage	V _R		1200	V			
Continuous forward current, per leg	I _F	T _C = 83 °C	45	٨			
Single pulse forward current, per leg	I _{FSM}	T _J = 25 °C	400	A			
	PD	T _C = 83 °C	139	W			
Maximum power dissipation, per leg		T _C = 100 °C	104	vv			
RMS isolation voltage	VISOL	Any terminal to case, t = 1 min	2500	V			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIO	NS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-		
		I _F = 25 A		-	2.46	3.0		
		I _F = 40 A	See fig. 1	-	2.68	3.3	V	
Ferward voltage	V _{FM}	I _F = 25 A, T _J = 125 °C		-	2.22	-		
Forward voltage		I _F = 40 A, T _J = 125 °C		-	2.52	-		
		I _F = 25 A, T _J = 150 °C		-	2.12	2.55		
		I _F = 40 A, T _J = 150 °C		-	2.43	2.96		
		$V_R = V_R$ rated		-	1.5	75	μA	
Reverse leakage current	I _{RM}	T_J = 125 °C, V_R = V_R rated	See fig. 2	-	0.5	2	mA	
		T_J = 150 °C, V_R = V_R rated		-	2	5		
Junction capacitance	CT	V _R = 1200 V	See fig. 3	-	30	-	pF	

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST C	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}/\mu \text{s}, V_R = 30 \text{ V}$		-	35	-			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	80	-	ns		
		T _J = 125 °C	1 40 4	-	130	-			
Peak recovery current	1	T _J = 25 °C	I _F = 40 A dI _F /dt = - 200 A/μs	-	6.8	-	А		
Feak recovery current	IRRM	T _J = 125 °C	$V_{\rm R} = 200 \text{ V}$	-	11.5	-	A		
Reverse recovery charge	Q _{rr}	T _J = 25 °C	vR - 200 v	-	270	-	nC		
		T _J = 125 °C		-	740	-	no		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction to case, single leg conducting	D		-	-	0.48		
Junction to case, both legs conducting	n thJC	R _{thJC}	-	-	0.24	°C/W	
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.10	-		
Weight			-	30	-	g	
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)	
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)	
Case style				SC)T-227		

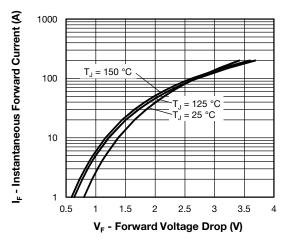


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

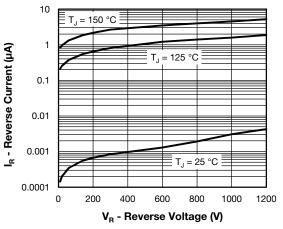


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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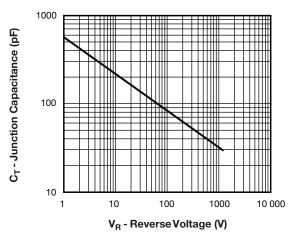


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

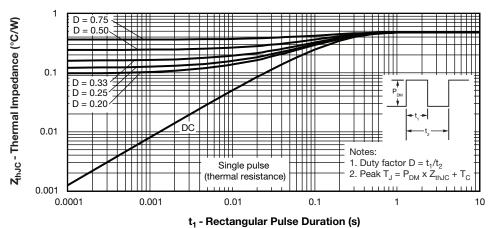


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

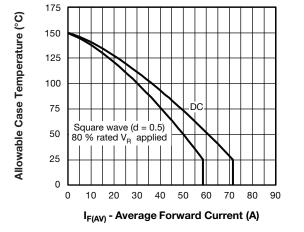
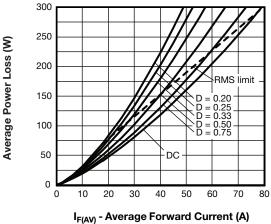


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)



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Fig. 6 - Forward Power Loss Characteristics (Per Leg)

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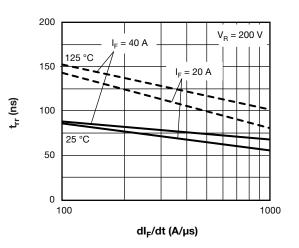
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Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

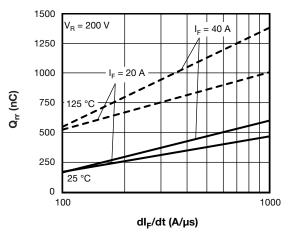


Fig. 8 - Typical Stored Charge vs. dl_F/dt

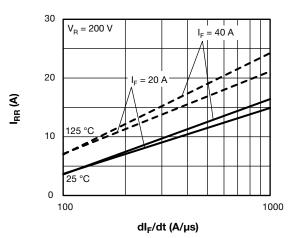


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt

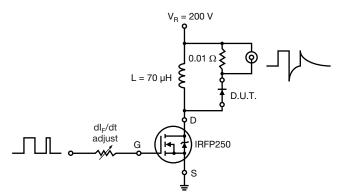
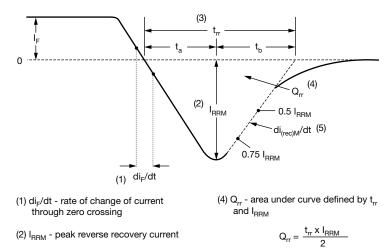


Fig. 10 - Reverse Recovery Parameter Test Circuit

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(2) I_{RBM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device code	VS-	HF	Α	90	F	Α	120		
	1	2	3	4	5	6	7		
	1 - 2 -		Vishay Semiconductors product HEXFRED [®] family						
	3 -	Pro	Process designator (A = electron irradiated)						
	4 -	Ave	Average current (90 = 90 A)						
	5 -	Circ	Circuit configuration (two separate diodes, parallel pin-out)						
	6 -	Pac	kage ind	dicator (SOT-22	7 stanc	lard ins	ulated base)	
	7 -	Volt	age rati	ng (120	= 1200	V)			

CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
two separate diodes, parallel pin-out	F	Lead Assignment			

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95423					
Packaging information	www.vishay.com/doc?95425					

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SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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